

# Lecture 18: LNA Design (contd.)

Note Title

7/26/2011

Last class:

- 1) Input match
  - 2) Output match
- } may require iteration

\*  $g_m$  &  $C_{gd}$  will cause input & output matches to depend on each other - Iteration

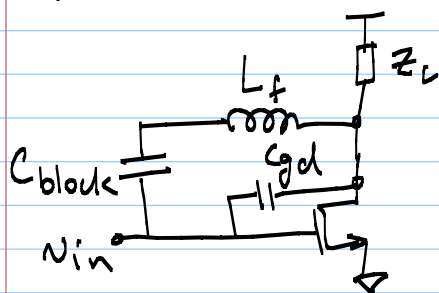
\* Input matching is quantified by  $S_{11}$  (also called 'return loss')

$$S_{11} = 20 \log \left| \frac{Z_{in} - R_s}{Z_{in} + R_s} \right|$$

\* Similarly, output matching is quantified by  $S_{22}$

3) stability: Circuit Techniques to improve stability (i.e. decrease  $C_{gd}$  and increase  $S_{12}$ )

A) Neutralisation:



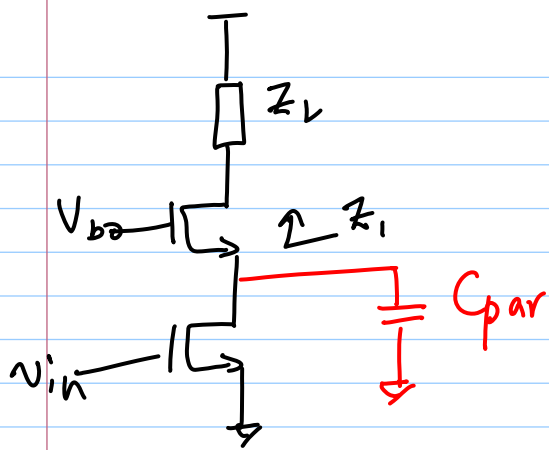
\*  $L_f$  and  $C_{gd}$  resonate @ desired frequency

\*  $L_f$  &  $C_{block}$  parasitics load input node

\* area intensive ( $L_f$ )

B) Cascode: \* reduces effect of  $C_{gd}$

\* reduces interaction between input & output tuned ckt's.



$$Z_1 = \frac{1}{g_m + g_{mb}} + \frac{Z_L}{(g_m + g_{mb})r_o}$$

assume  $r_o$  is large,  $g_m \gg g_{mb}$

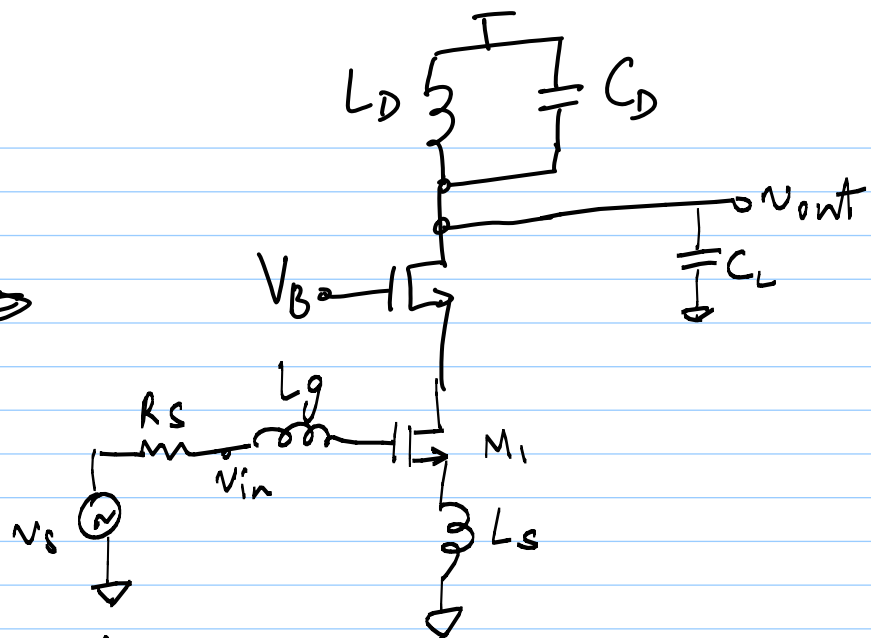
$$\Rightarrow Z_1 \approx \frac{1}{g_m}$$

\* parasitic cap can cause some loss of signal and degrade NF at high freq.

\* short-channel MOS -  $r_{out}$  is finite, so may want to use  $L > L_{min}$ .

→ This will increase  $C_{par}$

Cascode LNA  $\Rightarrow$



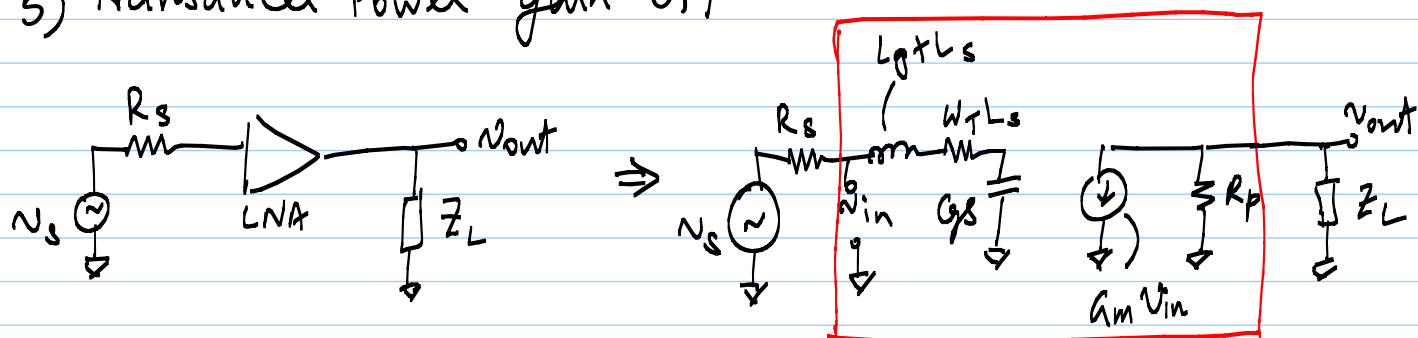
4) Voltage gain  $A_v$

$$A_v = \frac{v_{out}}{v_{in}} = G_m R_p$$

$$\Rightarrow |A_v = 2 Q_{in} g_{m1} R_p|$$

\* neglect  $r_{ds}$  (we will typically use a cascode)

## 5) Transducer Power gain $G_T$



$$G_T = \frac{\text{Power delivered to load}}{\text{Power available from source (max)}} = \frac{P_{\text{load}}}{P_{\text{avl},s}}$$

$$P_{\text{avl},s} = \frac{|v_{\text{in}}|^2}{2R_s} \quad \left\{ \begin{array}{l} \text{assume } v_{\text{in}}, v_{\text{out}} \text{ etc. are} \\ \text{peak values} \end{array} \right\}$$

$$\text{Let } Y_L = \frac{1}{Z_L} \Rightarrow G_L = \text{Re}(Y_L) = \text{Re}\left(\frac{1}{Z_L}\right)$$

$$\begin{aligned} P_{\text{load}} &= \frac{|V_{\text{out}}|^2}{2} \cdot G_L = \frac{|V_{\text{out}}|^2}{2} \cdot \text{Re}\left(\frac{1}{Z_L}\right) \\ &= \frac{1}{2} \text{Re}\left(\frac{1}{Z_L}\right) \cdot |G_m(R_p \parallel Z_L)|^2 \cdot |v_{\text{in}}|^2 \end{aligned}$$

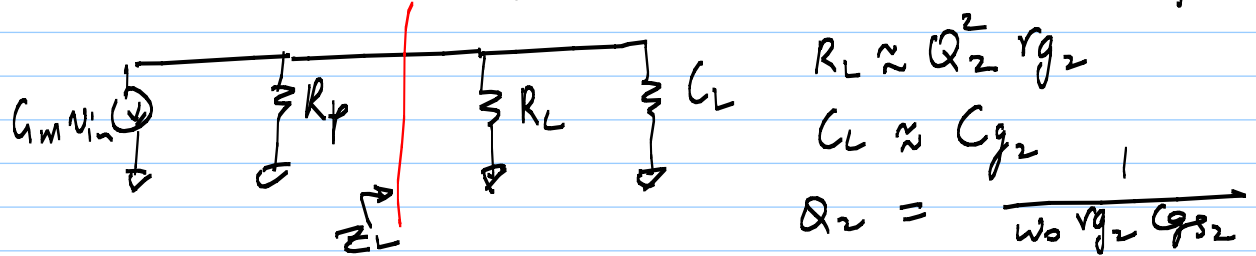
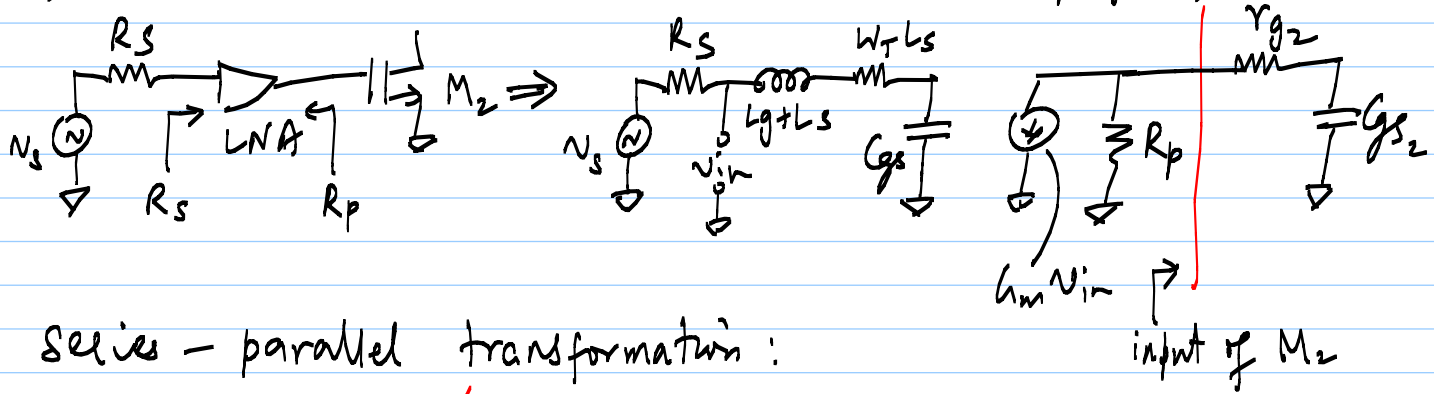
$$\Rightarrow \boxed{G_T = |G_m(R_p \parallel Z_L)|^2 \cdot R_s \cdot \text{Re}\left(\frac{1}{Z_L}\right)}$$

a) LNA drives off-chip component (e.g. filter)

$\rightarrow Z_L$  is matched to  $R_p$  in that case

$$G_T = \left| G_m \frac{R_p}{2} \right|^2 \cdot R_s \cdot \frac{1}{R_p} = \frac{G_m^2 R_s R_p}{4}$$

b) LNA drives mixer (or another amplifier)



- \* MOSFET with good layout  $\Rightarrow r_{g2}$  is very small
- \* Ideally  $r_{g2} \rightarrow 0 \Rightarrow Q_2 \rightarrow \infty \Rightarrow R_L \rightarrow \infty$

- \*  $C_L$  is usually absorbed into  $C_P$  (output tuning network of LNA)
- $\Rightarrow Z_L \approx R_L = Q_2^2 r_{g2}$

$$G_T = \left( G_m (R_P \parallel R_L) \right)^2 \cdot \frac{R_S}{R_L}$$

$$G_T \rightarrow 0 \text{ as } R_L \rightarrow \infty$$

What does this mean?

- $\rightarrow$  ideal MOSFET  $M_2$  has purely capacitive gate
- $\rightarrow$  no real power consumed @ input
- $\Rightarrow P_{load} \rightarrow 0 \Rightarrow A_T \rightarrow 0$

## 6) Available power gain $A_p$

$$A_p = \frac{\text{Power available from LNA output}}{\text{Power available from source}} = \frac{P_{av, LNA}}{P_{av, s}}$$

$P_{av, LNA} \equiv$  power delivered to load under matched condition (same as 4(a))

$$A_p = \frac{G_m^2 R_s R_p}{4}$$

How about Power Dissipation?

Power-constrained noise optimisation:

\* Minimise  $F$  given a specific bound on  $P_{diss}$ .

\* For full details, see Thomas Lee pp 380-384

From 2-port noise theory,

$$F = F_{min.} + \frac{R_n}{G_s} \left[ (G_s - G_{opt})^2 + (B_s - B_{opt})^2 \right]$$

\* define

$$\frac{G_{opt}}{\omega C_{gs}} = \alpha \sqrt{\frac{S}{S'} (1 - |c|^2)} = Q_{opt.}$$

$$Q_s \equiv \frac{1}{\omega C_{gs} R_s}$$

$$* \text{ Rewrite } F = F_{min.} + \left[ \frac{\gamma}{\alpha g_m R_s} \right] \left[ 1 - \frac{Q_{opt}^2}{Q_s^2} \right]$$

\* optimum  $Q_s$  turns out to be  $\approx \underline{\underline{4.5}}$

$$* W_{opt,p} = \frac{3}{2} \frac{1}{\omega L C_{ox} R_s Q_{sp}} \approx \frac{1}{3 \omega L C_{ox} R_s}$$

$$* F_{min,p} \approx 1 + 2.4 \frac{\gamma}{\alpha} \left[ \frac{W}{W_T} \right]$$

$$* F_{min} \approx 1 + 2.3 \left[ \frac{W}{W_T} \right]$$

$W_T/W$	$F_{min}$	$F_{min,p}$	$\gamma=2, \delta=4, \alpha=0.85$
20	0.5	1.1	
15	0.6	1.4	
10	0.9	1.9	
5	1.6	3.3	

basic design procedure:

- 1) Determine  $W_{opt,p}$  as above
- 2) Choose  $I_{bias}$  based on power constraint

- 3) Determine  $L_s$  (with  $R_{in}, W_T$  known)
- 4) Calculate  $NF_{min,p}$
- 5) Choose  $L_g$  for desired  $f_o$
- 6) Choose  $L_D$  to maximise  $R_p$  (highly dep. on process)  
and  $\therefore$  gain

Note: you will probably need to iterate at each step and also between steps

\* Noise vs. linearity trade off

as  $I_{bias} \uparrow \Rightarrow (V_{as} - V_T) \uparrow \Rightarrow IIP_3 \uparrow$

but  $\rightarrow$  increased short-channel effects

$\Rightarrow \alpha \left( \text{i.e. } \frac{g_m}{I_{D0}} \right) \downarrow \Rightarrow F \uparrow$